General Purpose Transistors

PNP Bipolar Junction Transistor

NOTE: Voltage and Current are negative for the PNP Transistor.

Features

• These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	V _{CEO}	30	V	
Collector-Base Voltage	V _{CBO}	40	V	
Emitter-Base Voltage	V _{EBO}	5.0	V	
Collector Current	I _C	700	mA	
Base Current	Ι _Β	350	mA	
Total Power Dissipation @ T_C = 25°C Total Power Dissipation @ T_C = 85°C Thermal Resistance, Junction–to–Ambient (Note 1)	P _D P _D R _θ JA	342 178 366	mW mW °C/W	
Total Power Dissipation @ T _C = 25°C Total Power Dissipation @ T _C = 85°C Thermal Resistance, Junction–to–Ambient (Note 2)	P _D P _D R _{θJA}	665 346 188	mW mW °C/W	
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

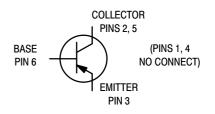
- Minimum FR-4 or G-10 PCB, Operating to Steady State.
- Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided), Operating to Steady State.



ON Semiconductor®

http://onsemi.com

0.7 AMPERES 30 VOLTS - V_{(BR)CEO} 342 mW





SC-74 CASE 318F STYLE 2

MARKING DIAGRAM



DB = Device Code

M = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT2131T1G	SC-74 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

,						
Characteri	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Collector - Base Breakdown Voltage	$(I_C = 100 \mu A)$	V _{(BR)CBO}	40	_	-	V
Collector – Emitter Breakdown Voltage (I _C = 10 mA)			30	-	-	V
Emitter-Base Breakdown Voltage	$(I_E = 100 \mu A)$	V _{(BR)EBO}	5.0	-	-	V
Collector Cutoff Current ($(V_{CB} = 25 \text{ V}, I_E = 0 \text{ A})$ $V_{CB} = 25 \text{ V}, I_E = 0 \text{ A}, T_A = 125^{\circ}\text{C})$	Ісво	- -	- -	1.0 10	μΑ
Emitter Cutoff Current	$(V_{EB} = 5.0 \text{ V}, I_{C} = 0 \text{ A})$	I _{EBO}	=	-	10	μΑ
ON CHARACTERISTICS						
DC Current Gain	$(V_{CE} = 3.0 \text{ V}, I_{C} = 100 \text{ mA})$	h _{FE}	150	_	-	V
Collector - Emitter Saturation Voltage	$(I_C = 500 \text{ mA}, I_B = 50 \text{ mA})$	V _{CE(sat)}	=	-	0.25	V
Collector - Emitter Saturation Voltage	(I _C = 700 mA, I _B = 70 mA)	V _{CE(sat)}	=	-	0.4	V
Base-Emitter Saturation Voltage (I _C = 700 mA, I _B = 70 mA)		V _{BE(sat)}	=	-	1.1	V
Collector-Emitter Saturation Voltage	$(I_C = 700 \text{ mA}, V_{CE} = 1.0 \text{ V})$	V _{BE(on)}	-	_	1.0	V

TYPICAL CHARACTERISTICS

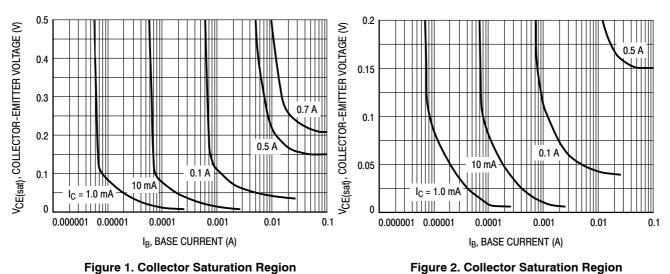


Figure 1. Collector Saturation Region

1000 1.0 V_{BE(sat)} $V_{CE} = 3.0 \text{ V}$ h FE, DC CURRENT GAIN VOLTAGE (V) 150°C 0.1 $25^{\circ}C$ -40°C V_{CE(sat)} $I_C/I_B = 10$ 100 0.01 0.01 1.0 0.001 1.0 I_C, COLLECTOR CURRENT (A) I_C, COLLECTOR CURRENT (A)

Figure 3. DC Current Gain

Figure 4. "ON" Voltages

TYPICAL CHARACTERISTICS

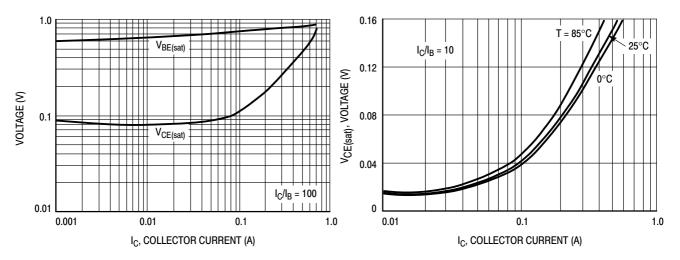


Figure 5. "ON" Voltages

Figure 6. Collector-Emitter Saturation Voltage

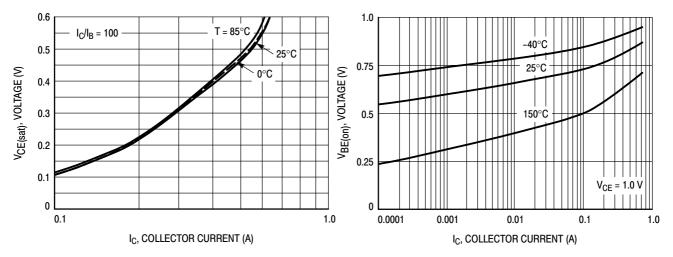


Figure 7. Collector-Emitter Saturation Voltage

Figure 8. V_{BE(on)} Voltage

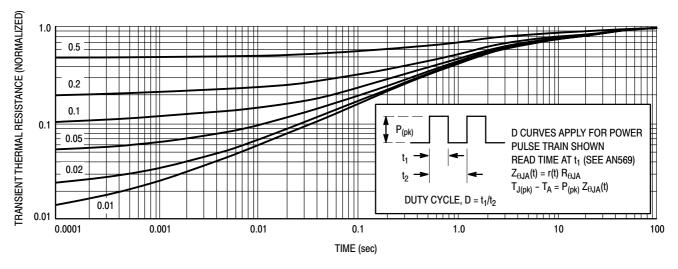
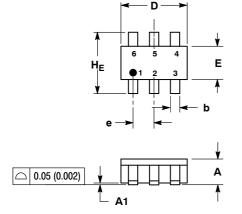
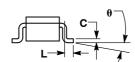


Figure 9. Thermal Response Curve

PACKAGE DIMENSIONS

SC-74 CASE 318F-05 **ISSUE N**





NOTES

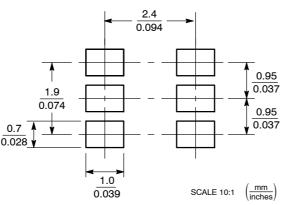
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 318F-01, -02, -03, -04 OBSOLETE. NEW STANDARD 318F-05.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.90	1.00	1.10	0.035	0.039	0.043
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.25	0.37	0.50	0.010	0.015	0.020
С	0.10	0.18	0.26	0.004	0.007	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
E	1.30	1.50	1.70	0.051	0.059	0.067
е	0.85	0.95	1.05	0.034	0.037	0.041
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.75	3.00	0.099	0.108	0.118
θ	0°	-	10°	0°	-	10°

- PIN 1. NO CONNECTION
 - 2. COLLECTOR 3. EMITTER

 - 4. NO CONNECTION 5. COLLECTOR
 - 6. BASE

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking, ited. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada

Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Phone: 421 33 790 2910

Phone: 81-3-5817-1050

Europe, Middle East and Africa Technical Support: Japan Customer Focus Center

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative